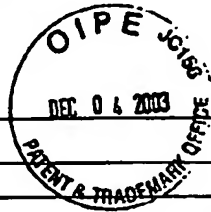


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Applicati n Number	10/043065
Filing Date	January 9, 2002
First Named Inventor	Forbes, Leonard
Group Art Unit	2822
Examiner Name	Meier, Stephen

Attorney Docket No: 303.684US3

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Examiner Initial *	USP Document Number	Publication Date	Name of Patentee or Applicant of cited Document	Class	Subclass	Filing Date if Appropriate
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Application Number	10/043065
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First Named Inventor	Forbes, Leonard
Group Art Unit	2822
Examiner Name	Rose, Kiesha

Sheet 1 of 1

Attorney Docket No: 303.684US3

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DATE CONSIDERED

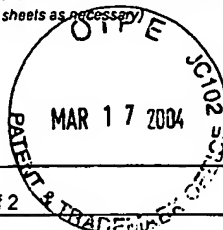
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Application Number 10/043065
 Filing Date January 9, 2002
 First Named Inventor Forbes, Leonard
 Group Art Unit 2822
 Examiner Name Rose, Kiesha

Attorney Docket No: 303.684US3

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I		FRANK, J. , et al., "Monte Carlo Simulations of p- and n-Channel Dual-Gate Si MOSFET's at the Limits of Scaling", <u>IEEE Transactions on Electron Devices, 40(11), (November 1993),pg. 2103</u>	
I		HIRAYAMA, M. , et al., "Low-Temperature Growth of High-Integrity Silicon Oxide Films by Oxygen Radical Generated in High-Density Krypton Plasma", <u>IEEE, (1999),4 pages</u>	
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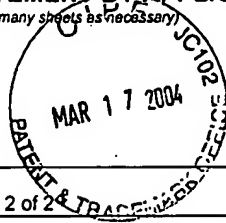
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Application Number	10/043065
Filing Date	January 9, 2002
First Named Inventor	Forbes, Leonard
Group Art Unit	2822
Examiner Name	Rose, Kiesha

Attorney Docket No: 303.684US3

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I		OHGURO, T., "Tenth Micron P-MOSFET's with Ultra-Thin Epitaxial Channel Layer Grown by Ultra-High-Vacuum CVD", <u>Proceedings: International Electron Devices Meeting, IEEE, Washington, Dec. 5-8, 1993, (Dec. 5, 1993), pp. 433-436</u>	
I		STRASS, A., et al., "Fabrication and Characterisation of thin low-temperature MBE-compatible silicon oxides of different stoichiometry", <u>Thin Solid Films</u> 349, (1999), pp. 135-146	
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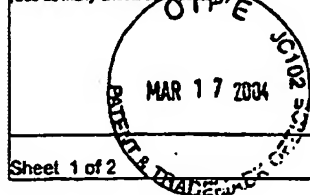
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	US-6,515,328	02/04/2003	Yang, W. , et al.	257	315	02/04/1999
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		FRANK, J. , et al., "Monte Carlo Simulations of p- and n-Channel Dual-Gate Si MOSFET's at the Limits of Scaling", <u>IEEE Transactions on Electron Devices, 40(11), (November 1993), pp. 2103</u>	
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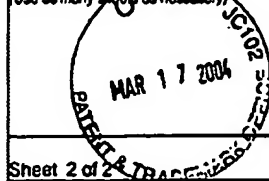
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Application Number	10/043065
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Group Art Unit	2822
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Sheet 2 of 2

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